

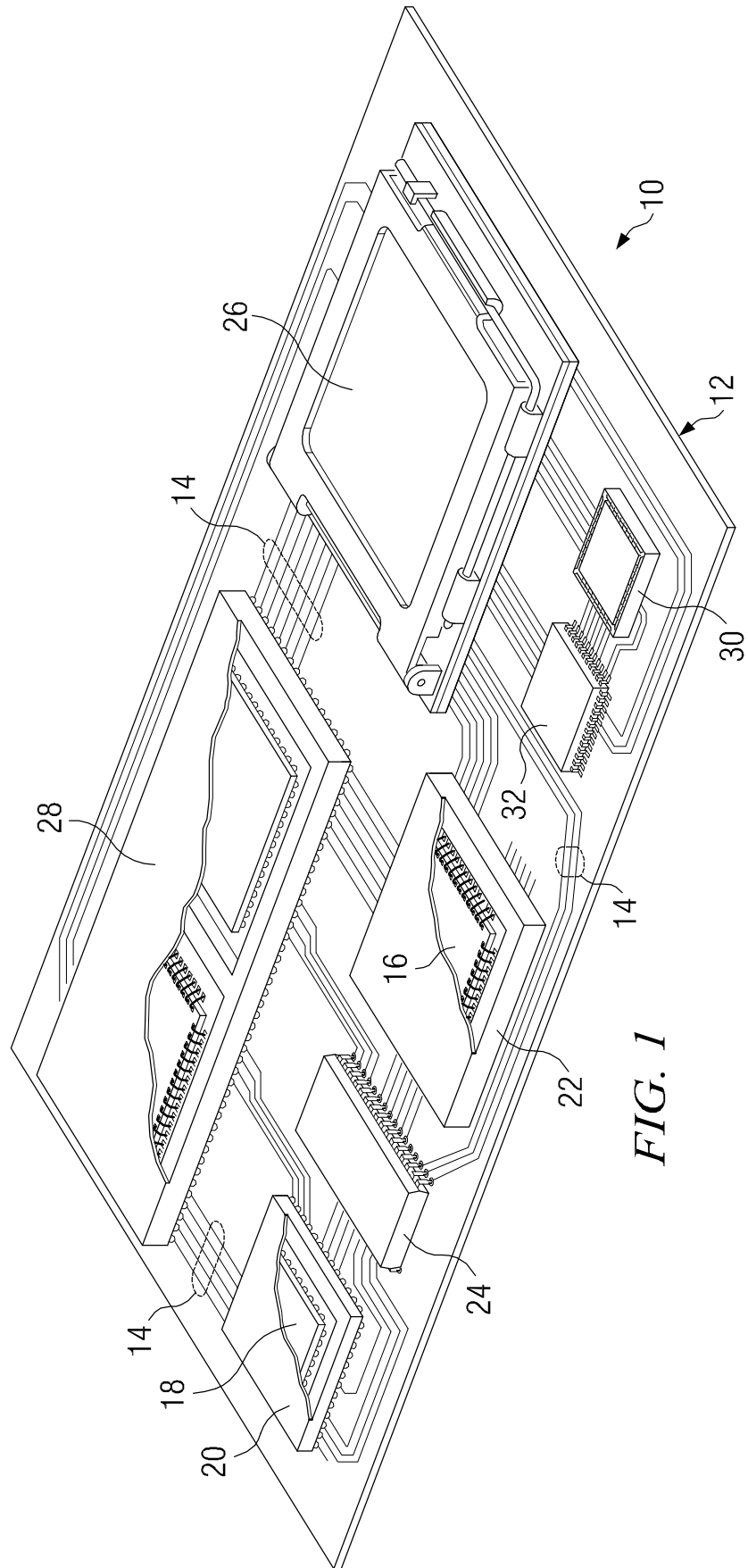
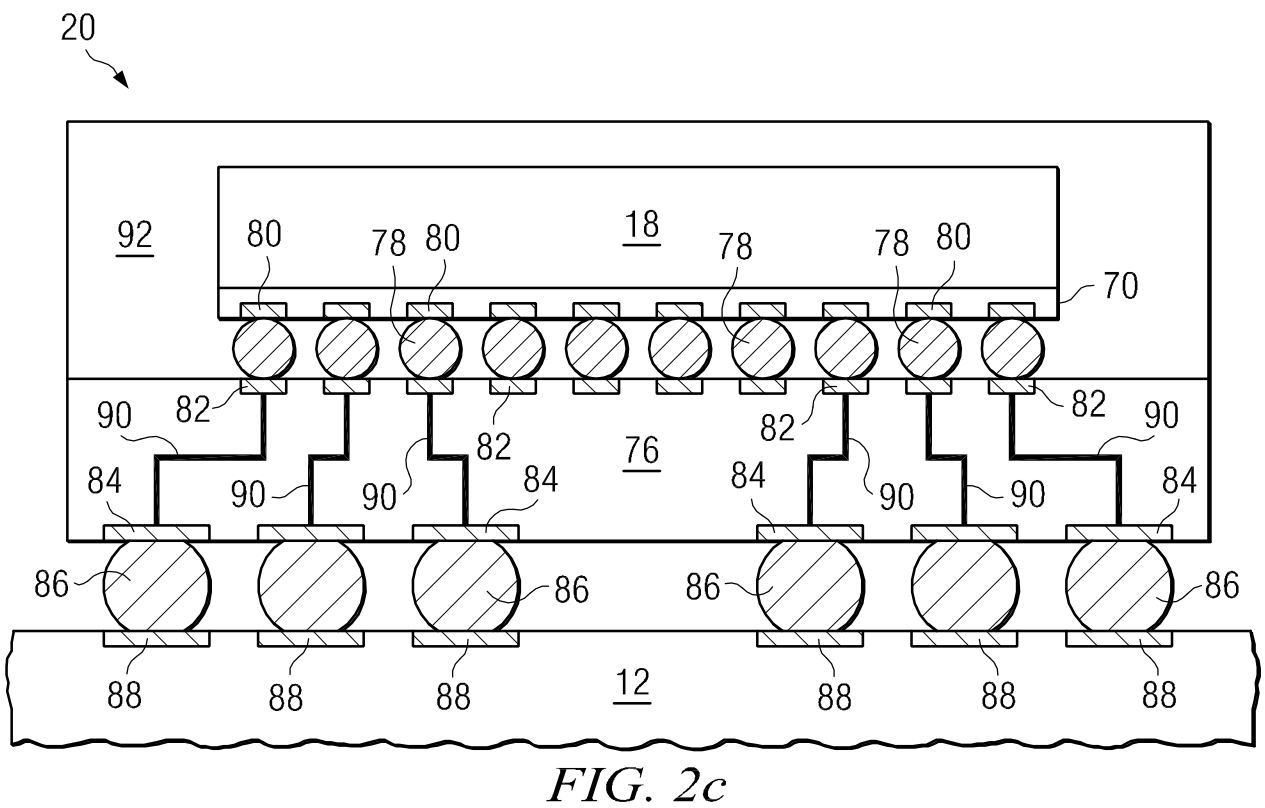
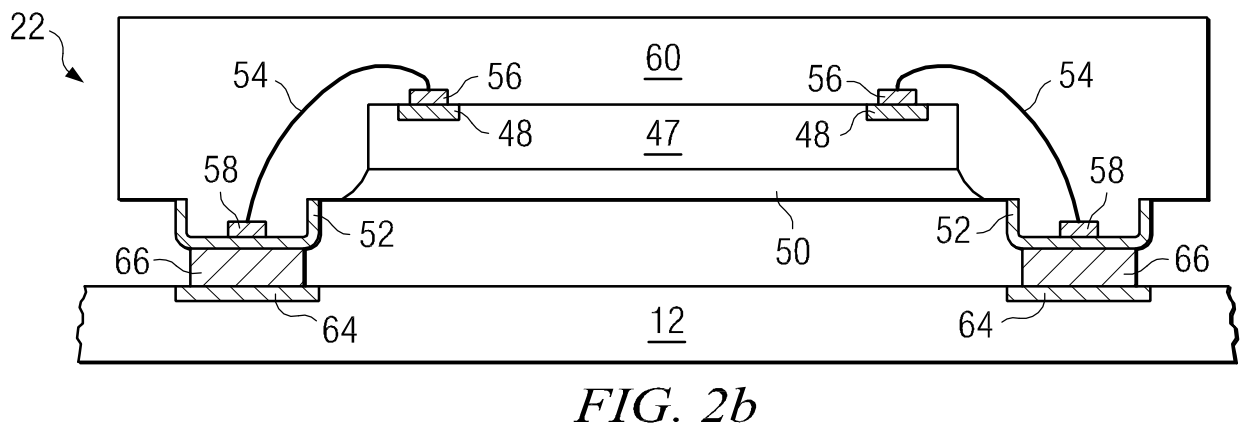
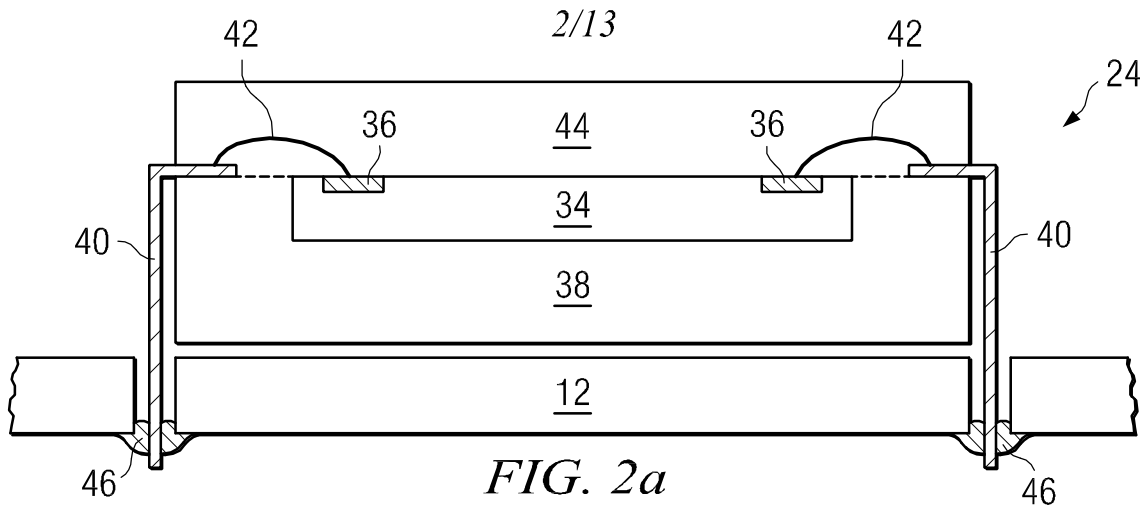


FIG. 1



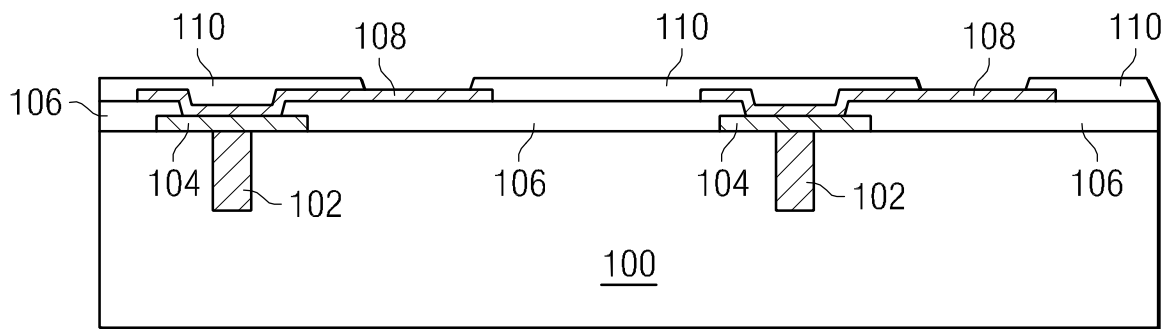


FIG. 3a

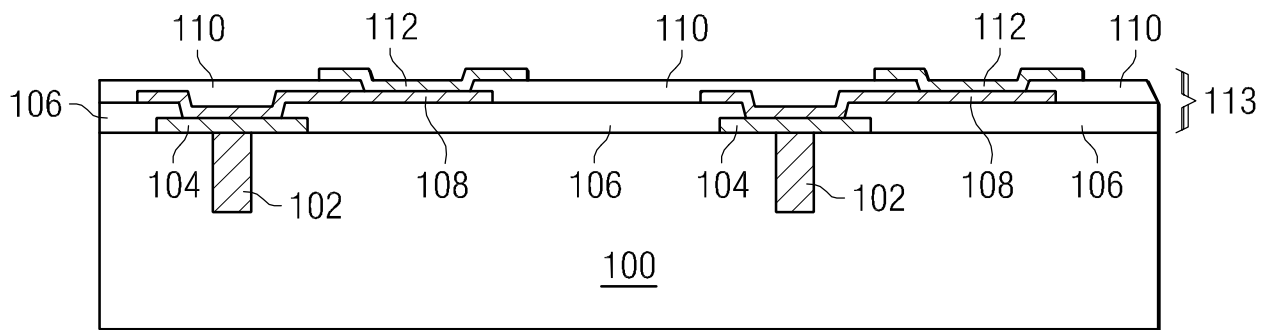


FIG. 3b

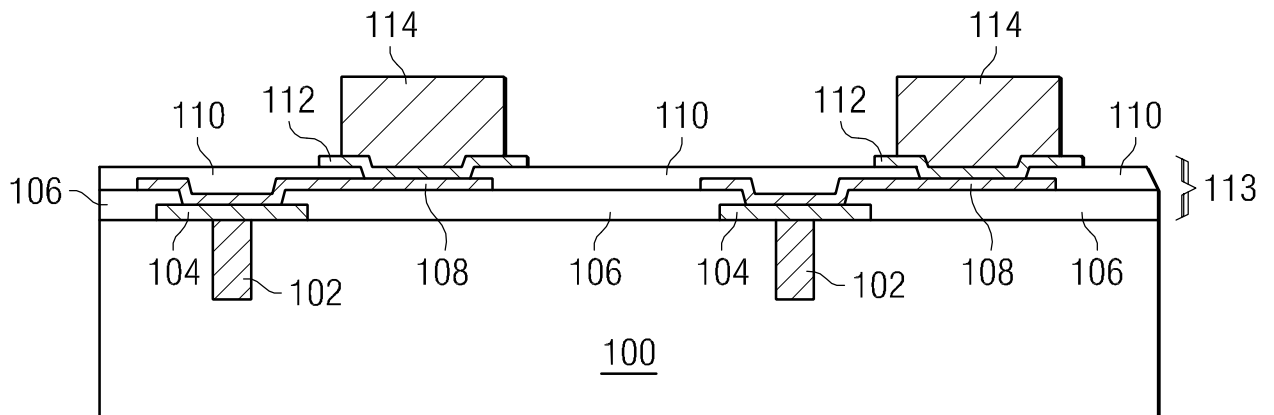


FIG. 3c

This cross-sectional view shows a semiconductor device with a central channel 110. The channel is flanked by two regions 112, which are further divided into sub-regions 114 and 116. The device is built on a substrate 100, with a base layer 102 and a top layer 106. A central layer 104 is also present. The device is shown in a perspective view, with a bracket 113 indicating the overall structure.

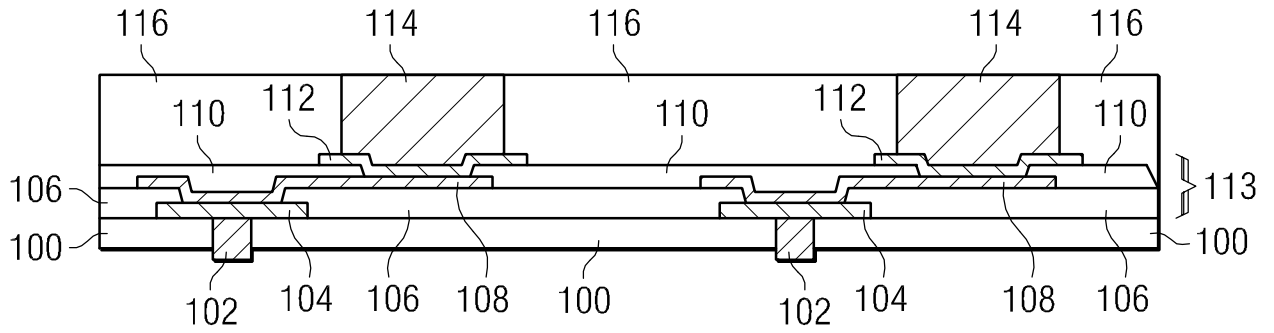


FIG. 3g

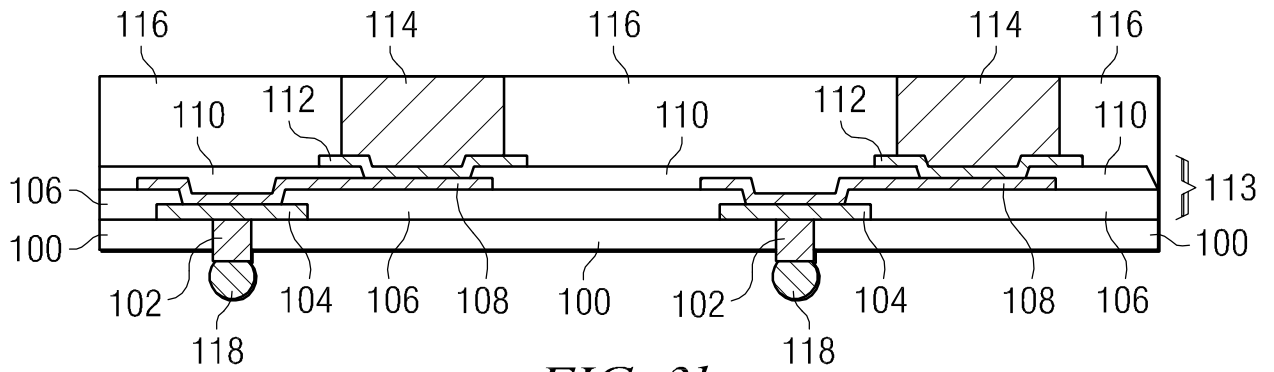


FIG. 3h

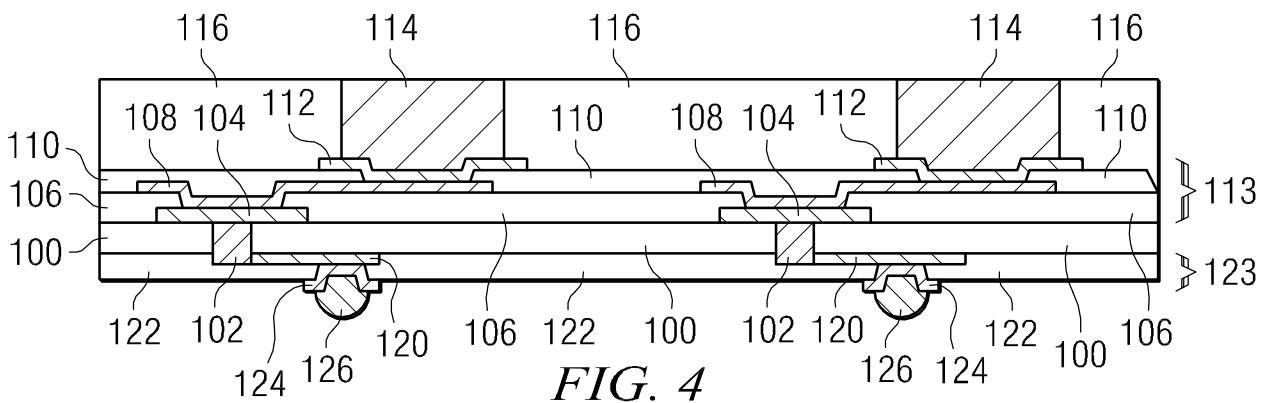
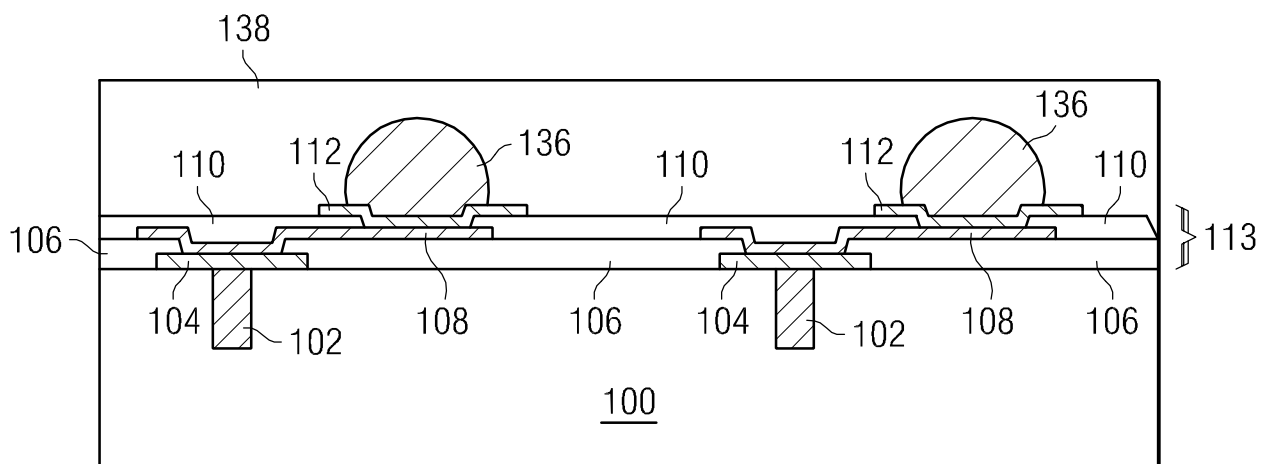
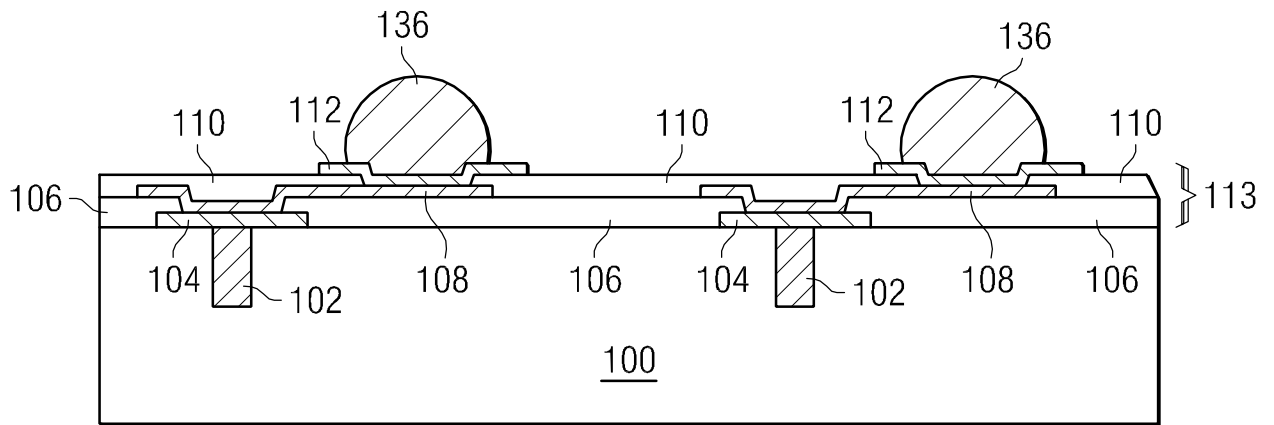
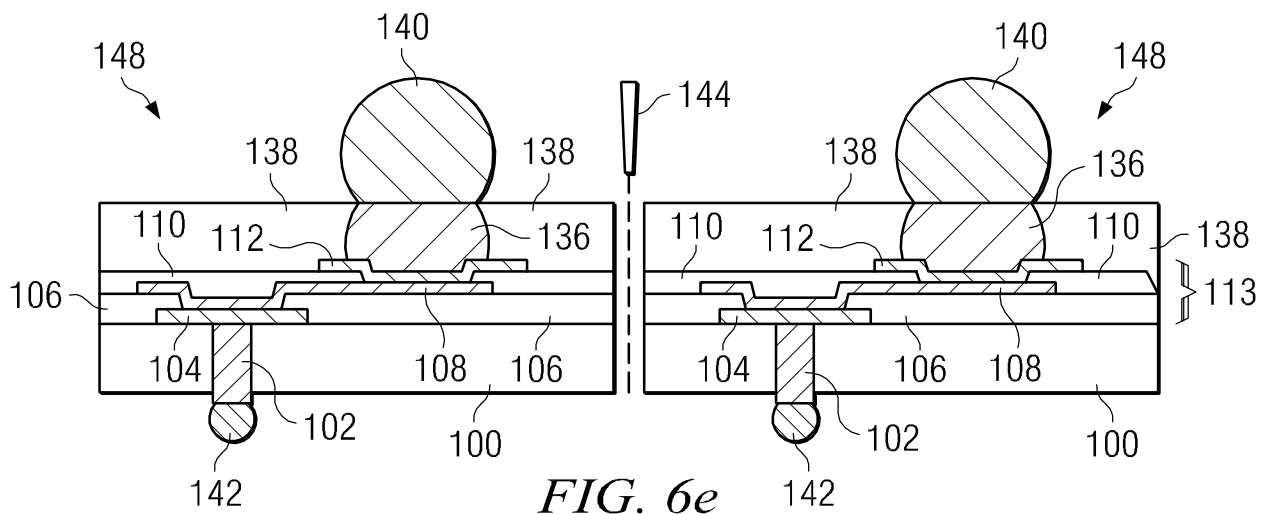
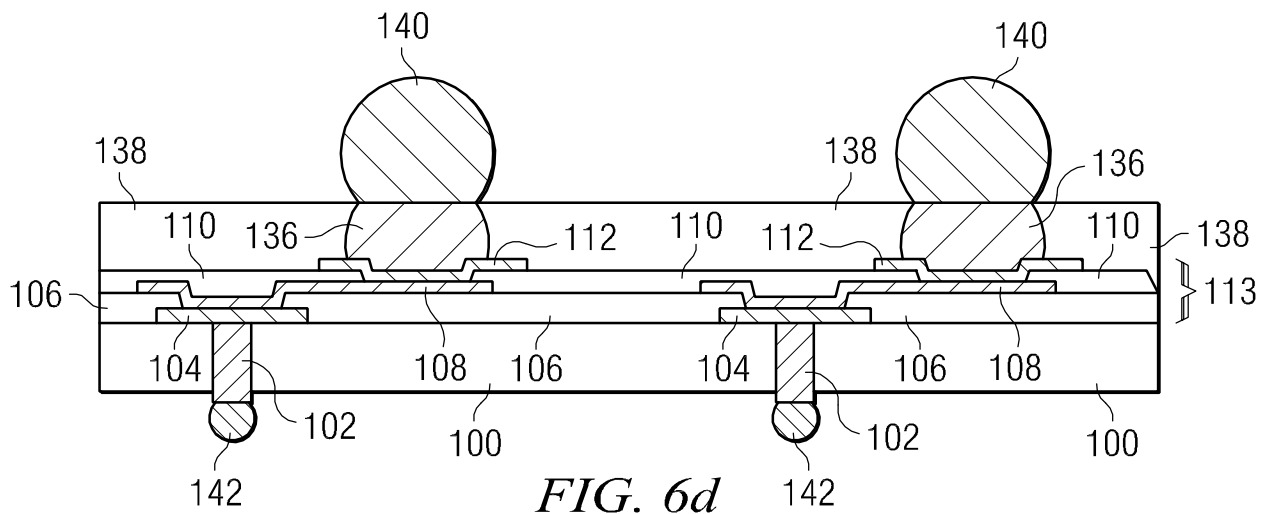
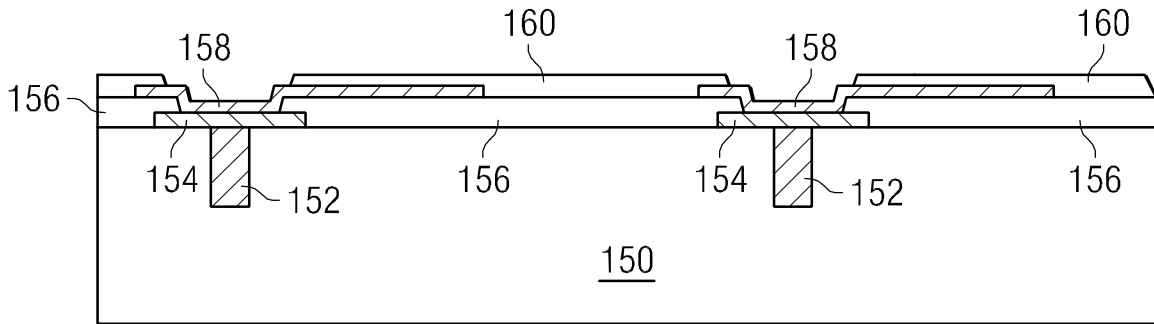


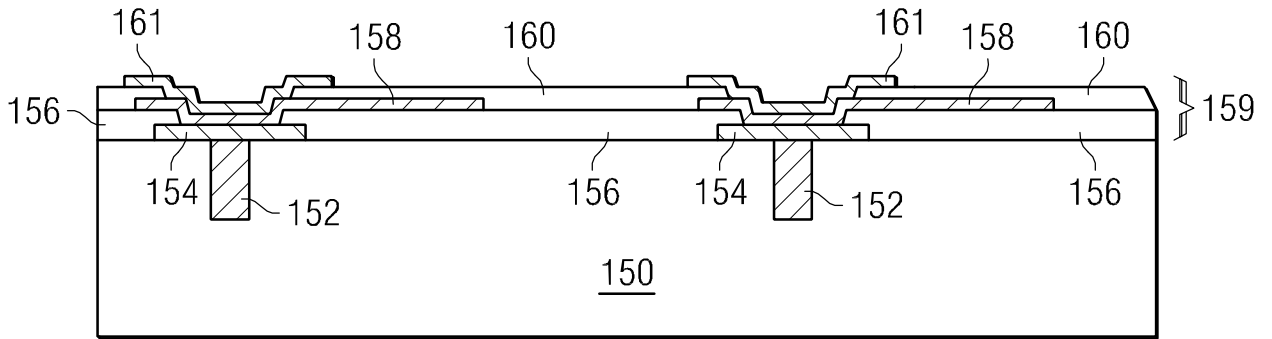
FIG. 4



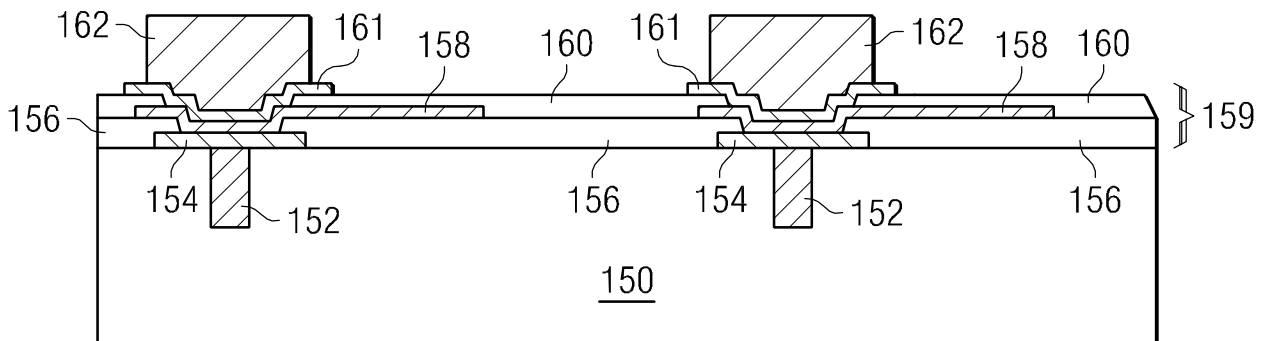




*FIG. 7a*



*FIG. 7b*



*FIG. 7c*

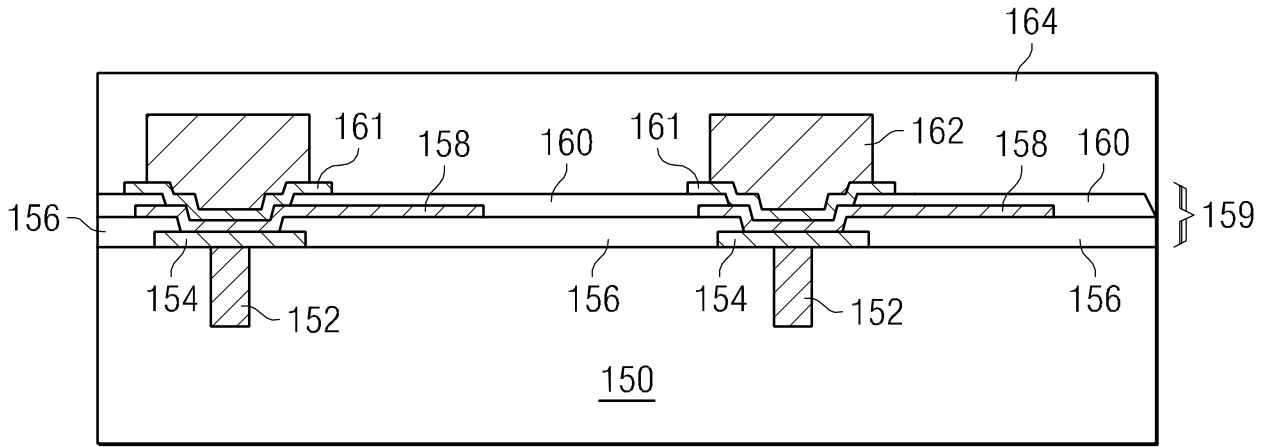


FIG. 7d

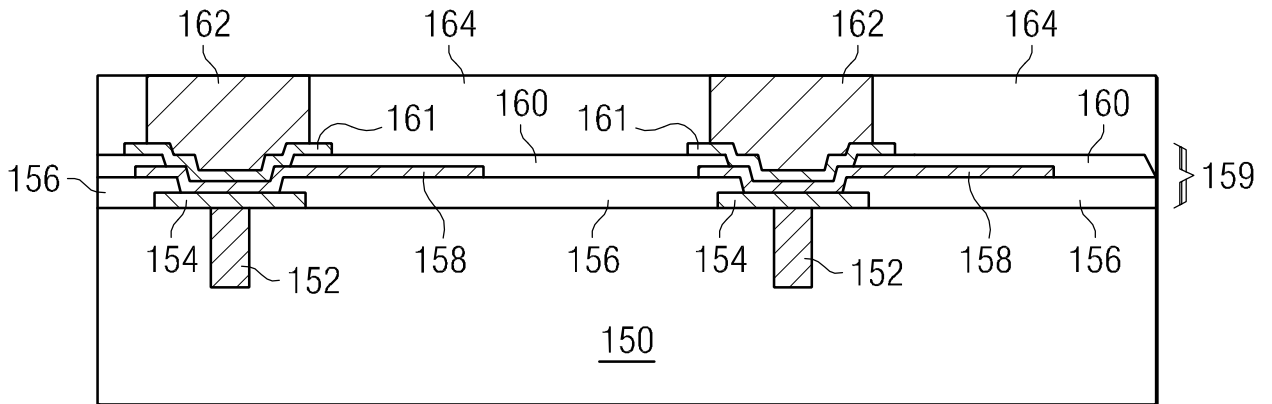


FIG. 7e

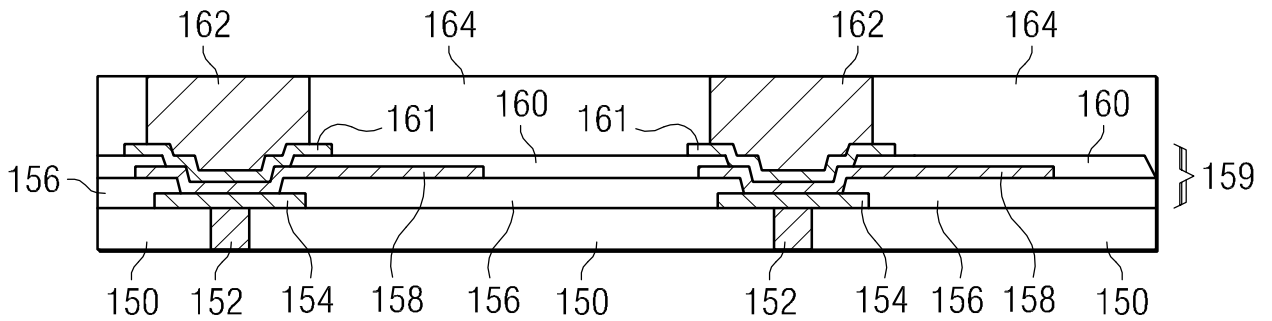


FIG. 7f

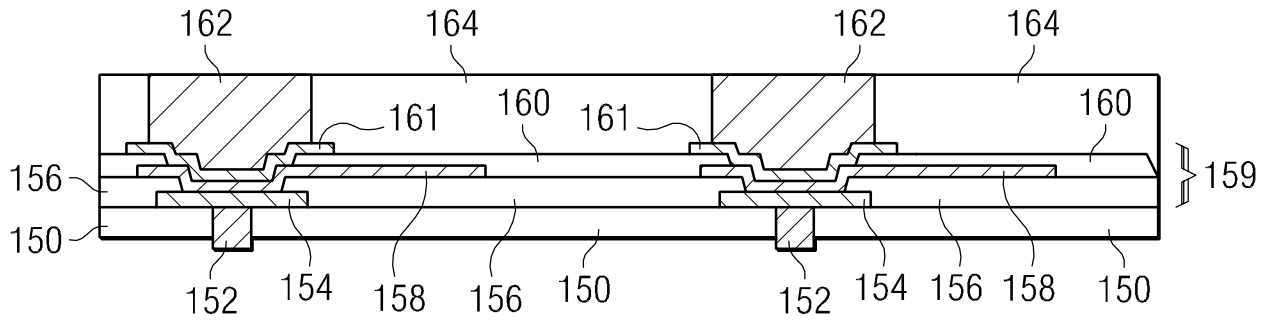


FIG. 7g

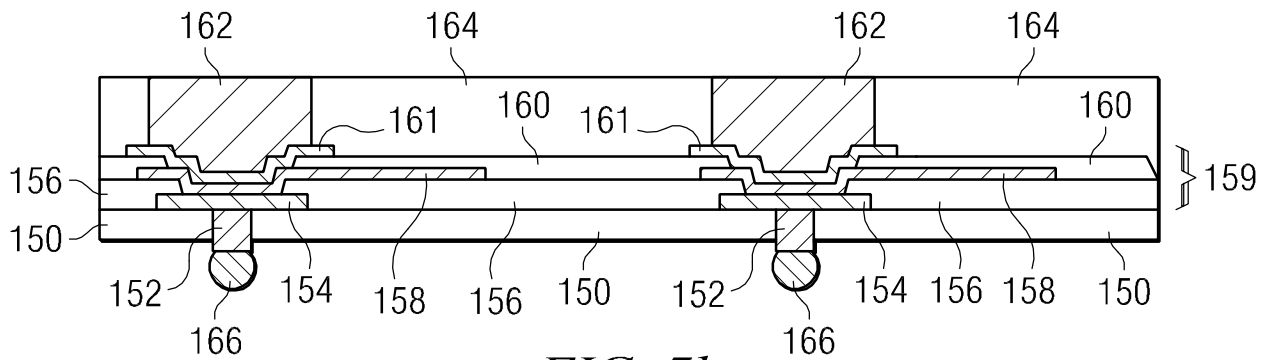


FIG. 7h

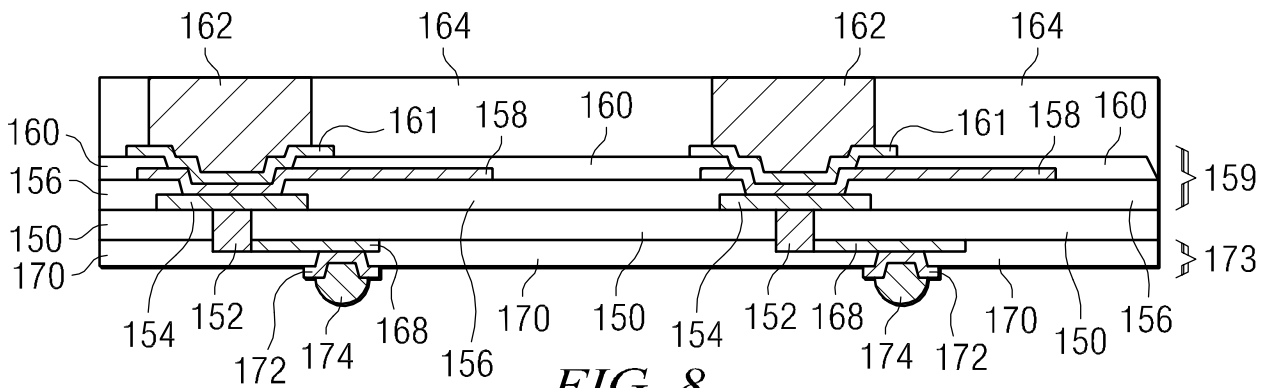
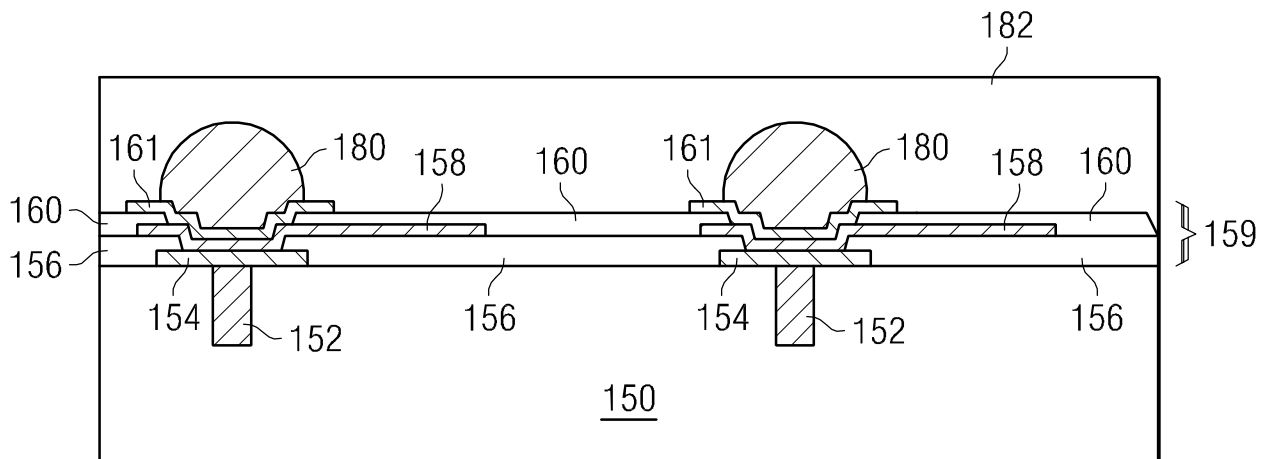
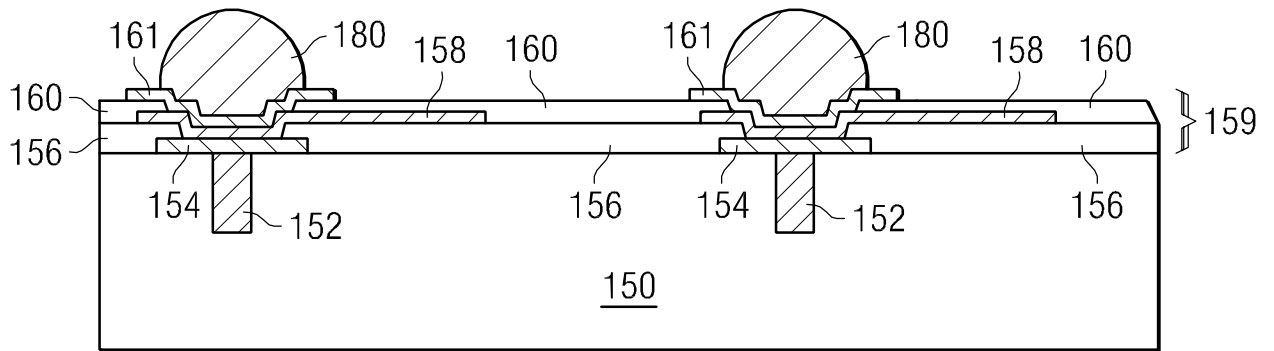


FIG. 8



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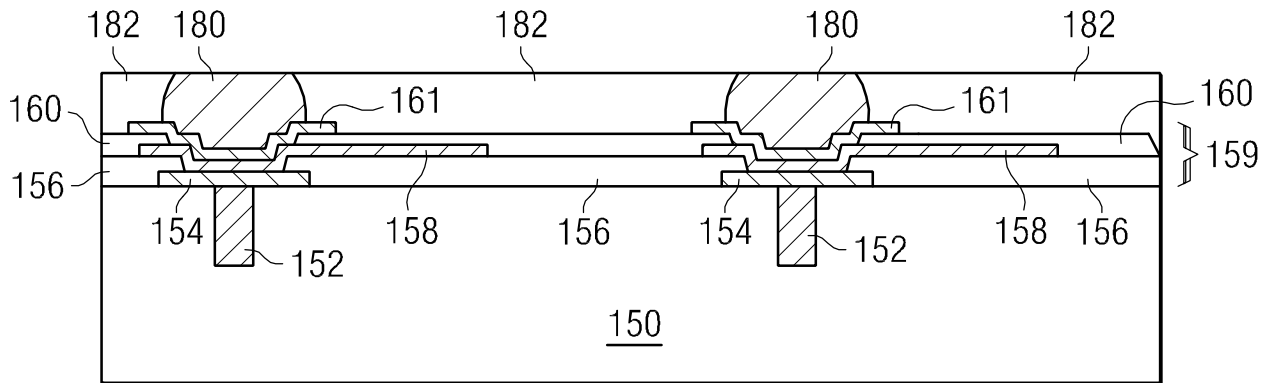


FIG. 10c

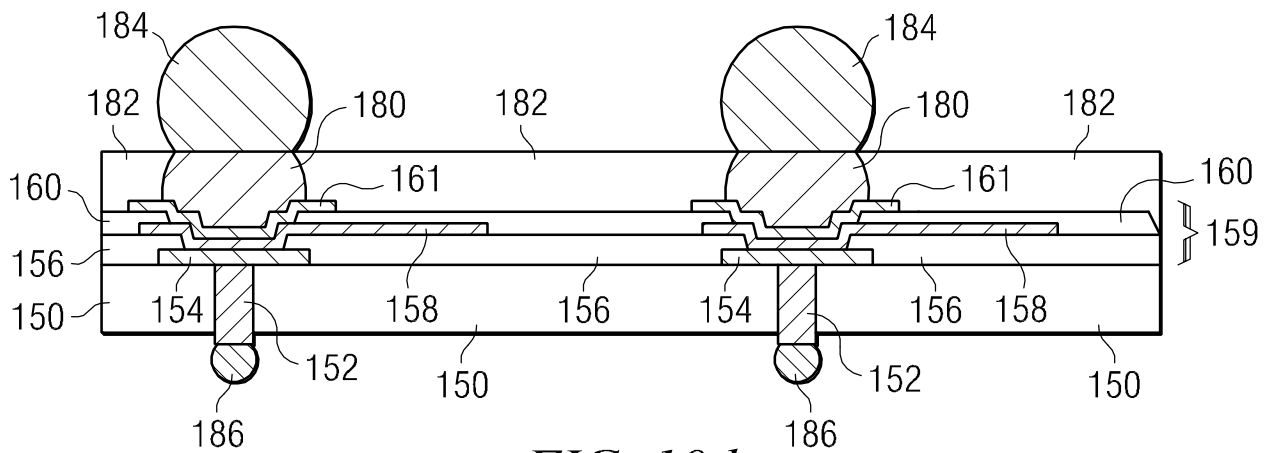


FIG. 10d

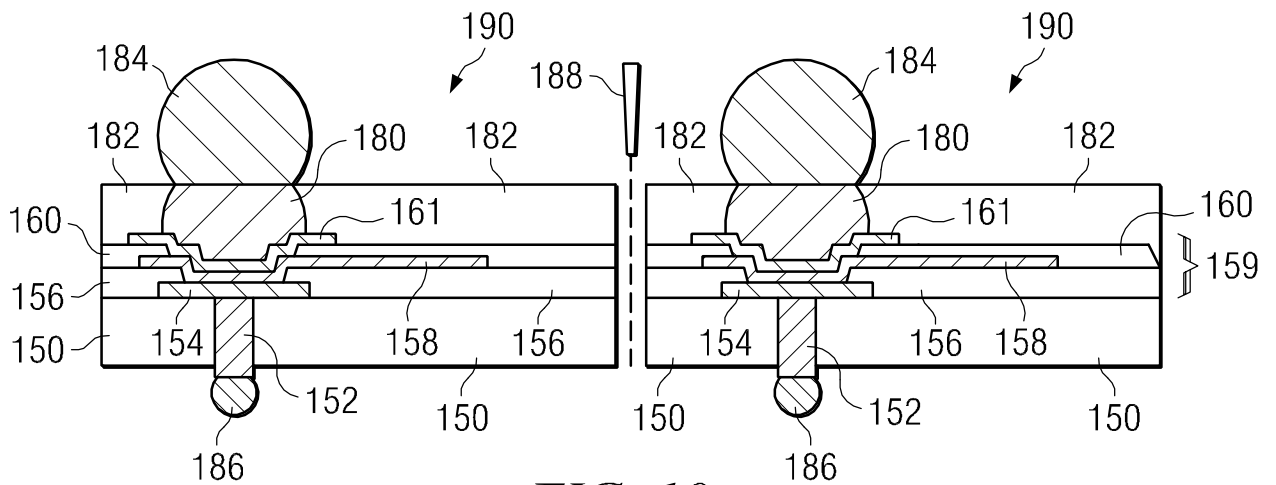


FIG. 10e

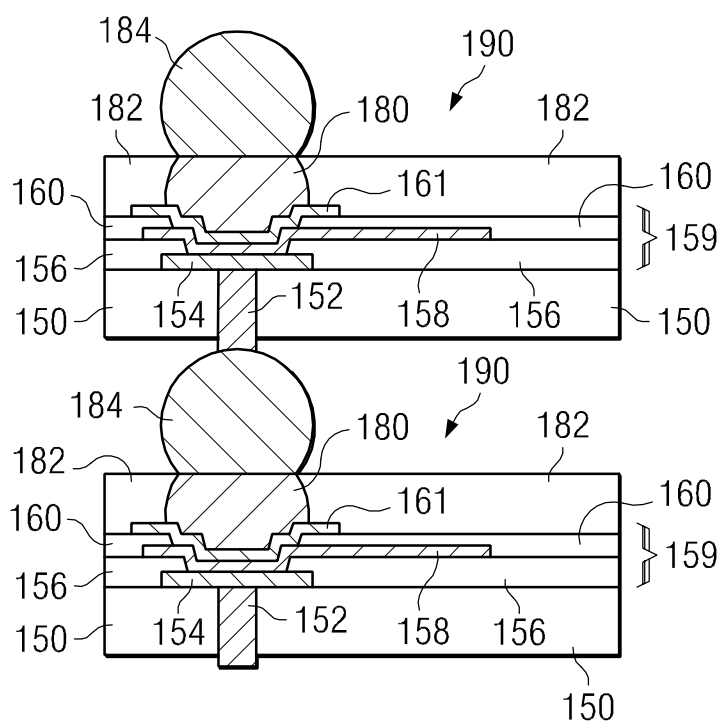


FIG. 11